

Silicon Switching Diode

1N914
or
1N914-1

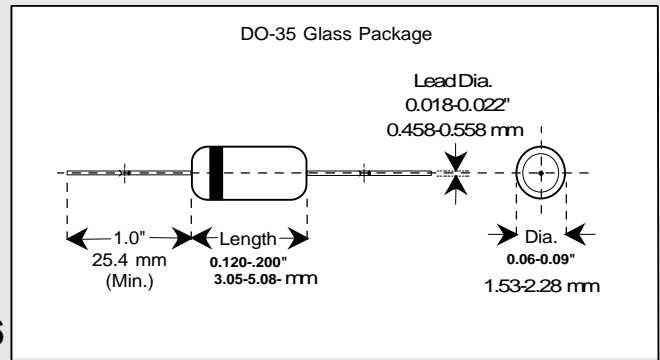
DO-35 Glass Package

Applications

Used in general purpose applications, where performance and switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Full approval to Mil-S-19500/116
- Available up to JANTXV levels
- "S" level screening available to SCDs



| Maximum Ratings | Symbol | Value | Unit |
|--|----------------|-------------|------------------|
| Peak Inverse Voltage | PIV | 100 (Min.) | Volts |
| Average Rectified Current | I_{Avg} | 75 | mAmps |
| Continuous Forward Current | I_{Fdc} | 300 | mAmps |
| Peak Surge Current ($t_{peak} = 1 \text{ sec.}$) | I_{peak} | 0.5 | Amp |
| Power Dissipation @ $T_L = 50 \text{ }^\circ\text{C}$, $L = 3/8"$ from body | P_{tot} | 250 | mWatts |
| Storage & Operating Temperature Range | $T_{St \& Op}$ | -65 to +200 | $^\circ\text{C}$ |

| Electrical Characteristics @ 25 $^\circ\text{C}$ * | Symbol | Absolute Limits | Unit |
|---|----------|-----------------|---------------|
| Breakdown Voltage @ $I_r = 0.1 \text{ mA}$ | PIV | 100 (Min) | Volts |
| Reverse Leakage Current @ $V_R = 20 \text{ V}$ | I_R | 0.025 (Max) | μA |
| Reverse Leakage ($V_r = 20 \text{ V}$, $150 \text{ }^\circ\text{C}$) | I_R | 50 (Max) | μA |
| Reverse Leakage Current @ $V_R = 75 \text{ V}$ | I_R | 5.0 (Max) | μA |
| Capacitance @ $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$ | C_T | 4.0 (Max) | pF |
| Reverse Recovery Time (note 1) | t_{rr} | 4.0 (Max) | nSecs |
| Forward Recovery Time (note 2) | V_{fr} | 2.5 (Max) | Volts |

Note 1: $I_F = 10 \text{ mA}$, $R_L = 100 \text{ Ohms}$, $V_r = 6.0 \text{ Volts}$, $I_{rr} = 1.0 \text{ mA}$

Note 2: $I_F = 50 \text{ mA dc}$

***UNLESS OTHERWISE SPECIFIED**